RoHS

COMPLIANT

HALOGEN FREE

Vishay Siliconix

P-Channel 20 V (D-S) MOSFET

PowerPAK® 0806 Single

Top View	Bottom View
SUMMARY	

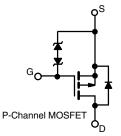
PRODUCT SUMMARY						
V _{DS} (V)	-20					
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5 \text{ V}$	1.25					
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -2.5 \text{ V}$	1.7					
$R_{DS(on)}$ max. (Ω) at V_{GS} = -1.8 V	2.7					
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.5 \text{ V}$	4.4					
Q _g typ. (nC)	0.64					
I _D (A)	-0.5 ^{a, f}					
Configuration	Single					

FEATURES

- TrenchFET® Gen III p-channel power MOSFET
- Ultra small 0.8 mm x 0.6 mm outline
- Ultra thin 0.4 mm max. height
- Typical ESD protection 1500 V (HBM)
- -1.5 V rated R_{DS(on)}
- 100% R_q tested
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- · Load switch
- · High speed switching
- Power management in battery-operated, mobile and wearable devices



ORDERING INFORMATION	
Package	PowerPAK 0806
Lead (Pb)-free and halogen-free	SiUD403ED-T1-GE3

The lead finish is NiPdAu and classed as E4 finish

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	-20	V	
Gate-source voltage		V_{GS}	± 8		
	T _A = 25 °C		-0.5 ^{a, f}		
Continuous drain surrent (T. 150 °C)	T _A = 70 °C	1 , [-0.5 ^{a, f}		
Continuous drain current (T _J = 150 °C)	T _A =25 °C	l _D	-0.4 ^b		
	T _A = 70 °C	1	-0.32 b	Α	
Pulsed drain current (t = 100 μs)		I _{DM}	-0.8		
	T _A = 25 °C		-0.5 ^{a, f}		
Continuous source-drain diode current	T _A = 70 °C	l _S	-0.37 b		
	T _A = 25 °C		1.25 ^a		
Maximum power dissipation	T _A = 70 °C	1 5	0.8 ^a	w	
	T _A = 25 °C	P _D	0.37 b	VV	
	T _A = 70 °C	ĺ	0.24 ^b		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature) c			260		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum junction-to-ambient a, d	+ < 5.0	В	80	100	°C/W	
Maximum junction-to-ambient b, e	t ≤ 5 s	R_{thJA}	265	335] 0/1	

Notes

- Surface mounted on 1" x 1" FR4 board with full copper, t = 5 s Surface mounted on 1" x 1" FR4 board with minimum copper, t = 5 s Refer to IPC / JEDEC® (J-STD-020), no manual or hand soldering Maximum under steady state conditions is 135 °C/W

- Maximum under steady state conditions is 400 °C/W
- Package limited



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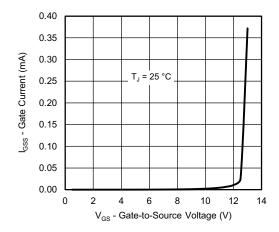
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static	1		L				
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20	-	-	V	
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$		-	-12.4	-		
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = -250 μA	_	1.6	-	mV/°C	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-0.4	-	-0.9	V	
Gate-source leakage		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$		-	± 0.5		
	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$	-	-	± 7	μA	
Zana a la callaca a lacia a canal		V _{DS} = -20 V, V _{GS} = 0 V	-	-	-1	μА	
Zero gate voltage drain current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V, T _J = 55 °C	-	-	-10		
On-state drain current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = 0 \text{ V}$	-0.5	-	-	Α	
		$V_{GS} = -4.5 \text{ V}, I_D = -0.3 \text{ A}$	-	1.01	1.25		
Data and a state with a second	5	$V_{GS} = -2.5 \text{ V}, I_D = -0.1 \text{ A}$	-	1.4	1.7		
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = -1.8 V, I _D = -0.1 A	-	2.1	2.7	Ω	
		$V_{GS} = -1.5 \text{ V}, I_D = -0.05 \text{ A}$	-	2.8	4.4	1	
Forward transconductance a	9 _{fs}	$V_{DS} = -10 \text{ V}, I_D = -0.3 \text{ A}$	-	0.6	-	S	
Dynamic ^b							
Input capacitance	C _{iss}		-	31	-		
Output capacitance	C _{oss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	8.1	-	pF	
Reverse transfer capacitance	C _{rss}		-	7	-		
Tatal anto about	Qg	$V_{DS} = -10 \text{ V}, V_{GS} = -8 \text{ V}, I_{D} = -0.3 \text{ A}$	-	1.1	1.7		
Total gate charge		$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -0.3 \text{ A}$	-	0.64	1	-0	
Gate-source charge	Q _{gs}	V _{DS} = -10 V, V _{GS} = -4.5 V, I _D = -0.3 A	-	0.13	-	nC	
Gate-drain charge	Q_{gd}	$v_{DS} = -10 \text{ v}, v_{GS} = -4.5 \text{ v}, i_{D} = -0.3 \text{ A}$	-	0.1	-		
Gate resistance	R_g	f = xx MHz	15	74	150	Ω	
Turn-on delay time	t _{d(on)}		-	7	15		
Rise time	t _r	$V_{DD} = -10 \text{ V}, R_L = 33.3 \Omega, I_D \cong -0.3 \text{ A},$	-	21	40		
Turn-off delay time	t _{d(off)}	V_{GEN} = -4.5 V, R_g = 1 Ω	-	11	20		
Fall time	t _f		-	11	20	200	
Turn-on delay time	t _{d(on)}		-	2	5	ns	
Rise time	t _r	$V_{DD} = -10 \text{ V}, R_L = 33.3 \Omega, I_D \cong -0.3 \text{ A},$	-	18	40		
Turn-off delay time	t _{d(off)}	$V_{GEN} = -8 \text{ V}, R_g = 1 \Omega$	-	10	20		
Fall time	t _f		-	10	20		
Drain-Source Body Diode Characteristi	cs						
Continuous source-drain diode current	I _S	T _A = 25 °C	-	-	-0.5 ^c	Α	
Pulse diode forward current	I _{SM}		-	-	-0.8		
Body diode voltage	V_{SD}	$I_S = -0.3 \text{ A}, V_{GS} = 0 \text{ V}$	-	-0.9	-1.2	V	
Body diode reverse recovery time	t _{rr}		-	15	30	ns	
Body diode reverse recovery charge	Q_{rr}	I _F = -0.3 A, di/dt = 100 A/μs,	-	7.5	15	nC	
Reverse recovery fall time	t _a	T _J = 25 °C	-	10.5	-	ne	
Reverse recovery rise time	t _b		-	4.5	-	ns	

Notes

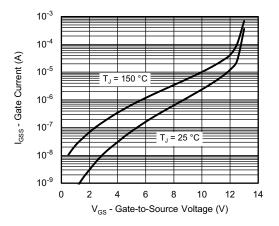
- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Surface mounted on 1" x 1" FR4 board with full copper, t = 5 s

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

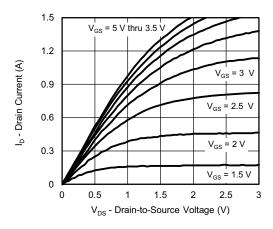




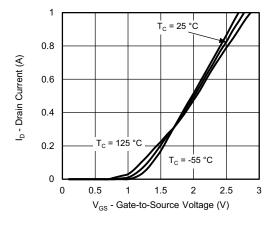
Gate Current vs. Gate-Source Voltage



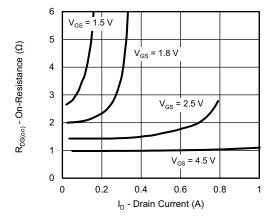
Gate Current vs. Gate-Source Voltage



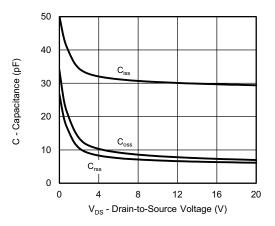
Output Characteristics



Transfer Characteristics

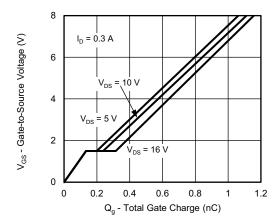


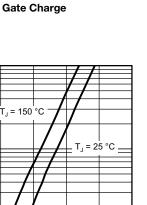
On-Resistance vs. Drain Current and Gate Voltage



Capacitance







1.2

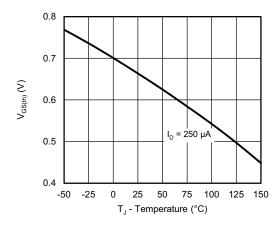
Source-Drain Diode Forward Voltage

0.6

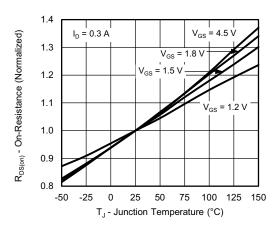
V_{SD} - Source-to-Drain Voltage (V)

0.8

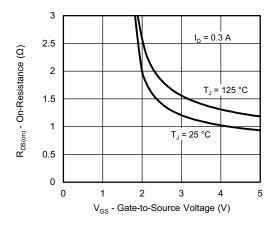
1.0



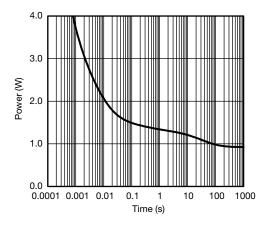
Threshold Voltage



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

I_S - Source Current (A)

0.1

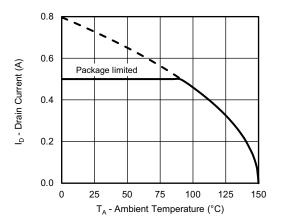
0.01

0

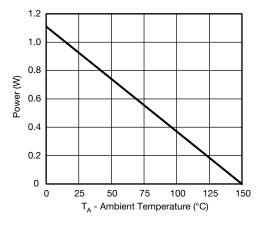
0.2

0.4

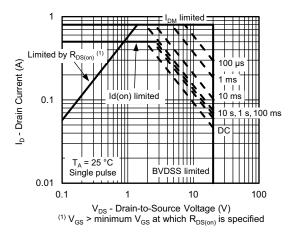




Current Derating a



Power, Junction-to-Ambient

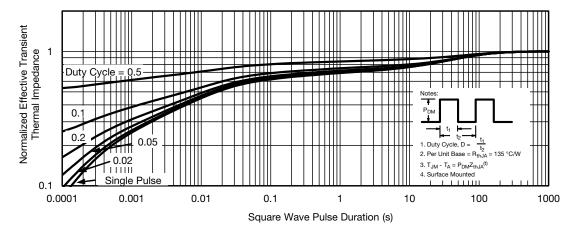


Safe Operating Area, Junction-to-Ambient

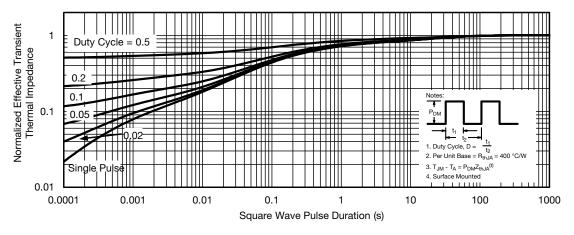
Note

a. The power dissipation P_D is based on T_J max. = 25 °C, using junction-to-ambient thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient (on 1" x 1" FR4 board with maximum copper)

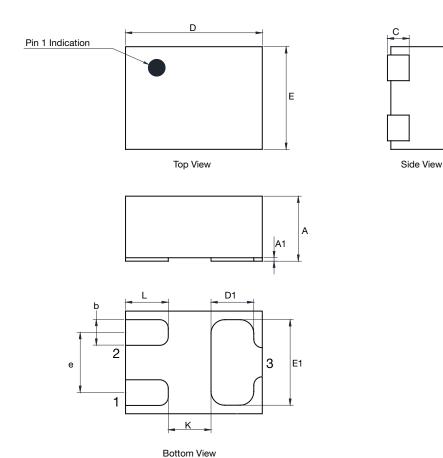


Normalized Thermal Transient Impedance, Junction-to-Ambient (on 1" x 1" FR4 board with minimum copper)

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?70731.



Case Outline for PowerPAK 0.8 mm x 0.6 mm



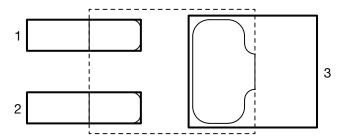
	MILLIMETERS			INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	0.350	0.380	0.400	0.0138	0.0150	0.0157
A1	0	-	0.020	0	-	0.0008
b	0.120	0.150	0.180	0.0047	0.0059	0.0071
С	0.119	0.127	0.135	0.0047	0.0050	0.0053
D	0.750	0.800	0.850	0.0295	0.0315	0.0335
D1	0.200	0.250	0.300	0.0078	0.0098	0.0118
E	0.550	0.600	0.650	0.0217	0.0236	0.0256
E1	0.450	0.500	0.550	0.0177	0.0197	0.0217
е	0.300	0.350	0.400	0.0118	0.0138	0.0158
K	0.150	0.250	0.350	0.0058	0.0098	0.0138
Ĺ	0.200	0.250	0.300	0.0078	0.0098	0.0118

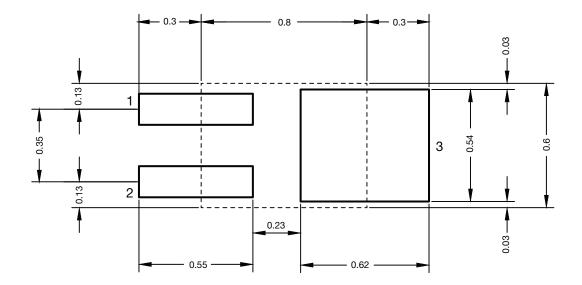
ECN: C13-1574-Rev. A, 23-Dec-13

DWG: 6020



Recommended Land Pattern PowerPAK® 0806







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Vishay

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